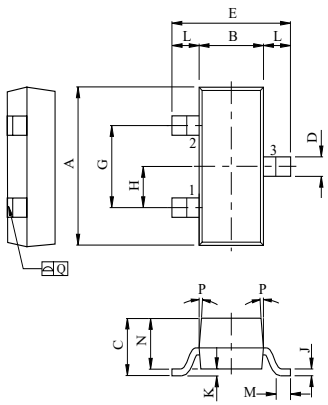
KTN2907S/AS

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES

- Low Leakage Current
  : I_{CEX}=-50nA(Max.) ; V_{CE}=-30V, V_{EB}=-0.5V.
- Low Saturation Voltage
  : $V_{CE(sat)}$=-0.4V(Max.) ; I_C=-150mA, I_B=-15mA.
- Complementary to the KTN2222S/2222AS.



DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.40+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7°
Q	0.1 MAX

1. EMITTER
2. BASE
3. COLLECTOR

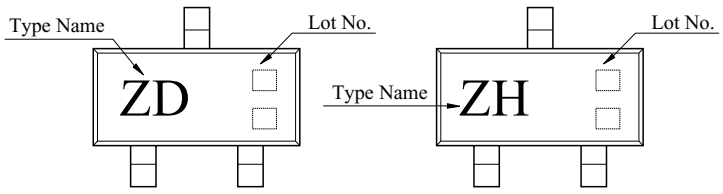
SOT-23

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING		UNIT
		KTN2907S	KTN2907AS	
Collector-Base Voltage	V_{CBO}	-60		V
Collector-Emitter Voltage	V_{CEO}	-40	-60	V
Emitter-Base Voltage	V_{EBO}	-5		V
Collector Current	I_C	-600		mA
Collector Power Dissipation (Ta=25℃)	P_C	350		mW
Junction Temperature	T_j	150		℃
Storage Temperature Range	T_{stg}	-55 150		℃

* Package Mounted On 99.5% Alumina 10x8x0.6mm.

Marking



MARK SPEC

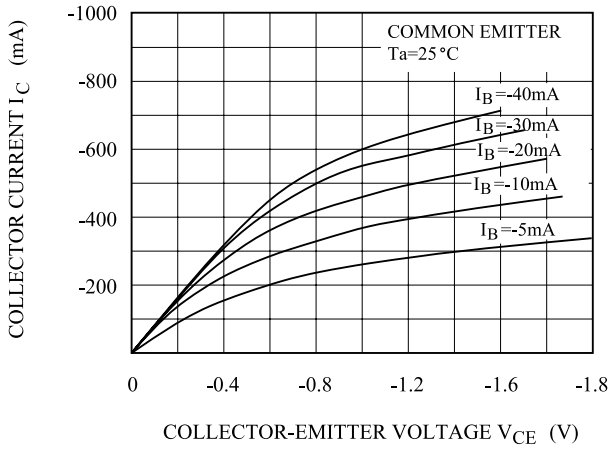
TYPE	MARK
KTN2907S	Z D
KTN2907AS	Z H

ELECTRICAL CHARACTERISTICS (Ta=25℃)

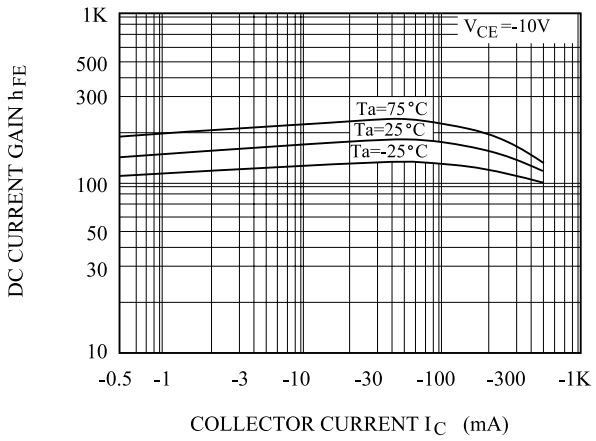
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CEX}	V_{CE}=-30V, V_{EB}=-0.5V	-	-	-50	nA
Collector Cut-off Current	KTN2907S	I_{CBO}	V_{CB}=-50V, I_E=0	-	-	-20	nA
	KTN2907AS			-	-	-10	
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	I_C=-10 μA, I_E=0	-60	-	-	V
Collector-Emitter Breakdown Voltage *	KTN2907S	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-40	-	-	V
	KTN2907AS			-60	-	-	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E=-10 μA, I_C=0	-5	-	-	V
DC Current Gain *	KTN2907S	h_{FE}(1)	I_C=-0.1mA, V_{CE}=-10V	35	-	-	
	KTN2907AS			75	-	-	
	KTN2907S	h_{FE}(2)	I_C=-1.0mA, V_{CE}=-10V	50	-	-	
	KTN2907AS			100	-	-	
	KTN2907S	h_{FE}(3)	I_C=-10mA, V_{CE}=-10V	75	-	-	
	KTN2907AS			100	-	-	
	KTN2907S	h_{FE}(4) *	I_C=-150mA, V_{CE}=-10V	100	-	300	
	KTN2907AS						
	KTN2907S	h_{FE}(5) *	I_C=-500mA, V_{CE}=-10V	30	-	-	
	KTN2907AS			50	-	-	
Collector-Emitter Saturation Voltage *		$V_{CE(sat)}$1	I_C=-150mA, I_B=-15mA	-	-	-0.4	V
		$V_{CE(sat)}$2	I_C=-500mA, I_B=-50mA	-	-	-1.6	
Base-Emitter Saturation Voltage *		$V_{BE(sat)}$1	I_C=-150mA, I_B=-15mA	-	-	-1.3	V
		$V_{BE(sat)}$2	I_C=-500mA, I_B=-50mA	-	-	-2.6	
Transition Frequency		f_T	V_{CE}=-20V, I_C=-50mA, f=100MHz	200	-	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	-	8	pF
Input Capacitance		C_{ib}	V_{BE}=-2V, I_C=0, f=1.0MHz	-	-	30	pF
Switching Time	Turn-On Time	t_{on}	V_{CC}=-30V, I_C=-150mA, I_{B1}=-15mA	-	-	45	nS
	Delay Time	t_d		-	-	10	
	Rise Time	t_r		-	-	40	
	Turn-Off Time	t_{off}	V_{CC}=-6V, I_C=-150mA, I_{B1}=-I_{B2}=-15mA	-	-	100	
	Storage Time	t_{stg}		-	-	80	
	Fall Time	t_f		-	-	30	

* Pulse Test : Pulse Width≦300 μS, Duty Cycle≦2%.

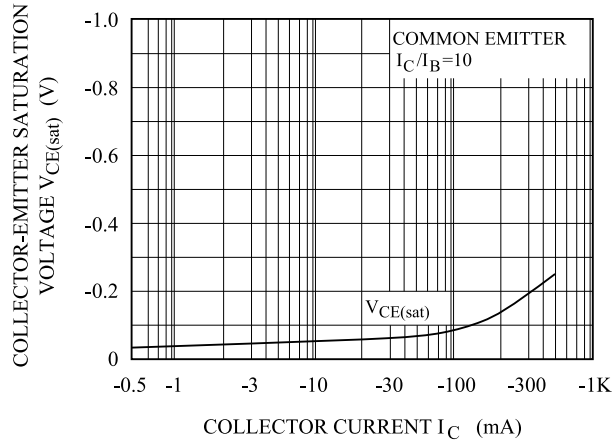
I_C - V_{CE}



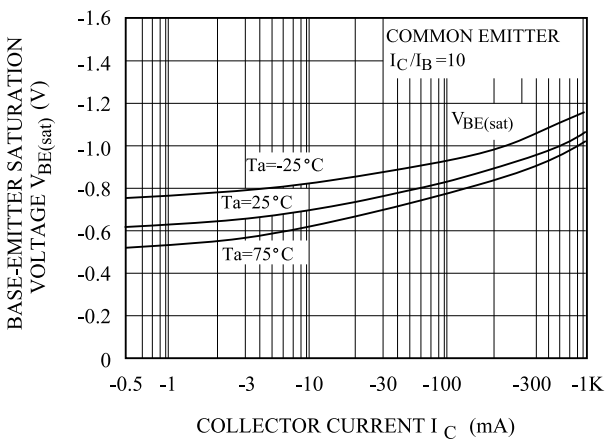
h_{FE} - I_C



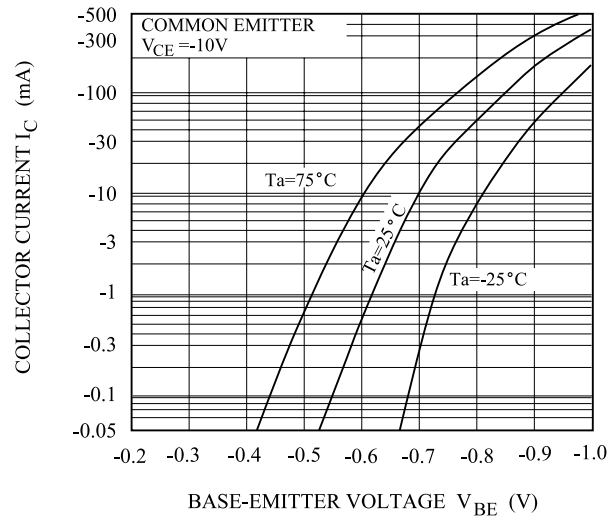
$V_{CE(sat)}$ - I_C



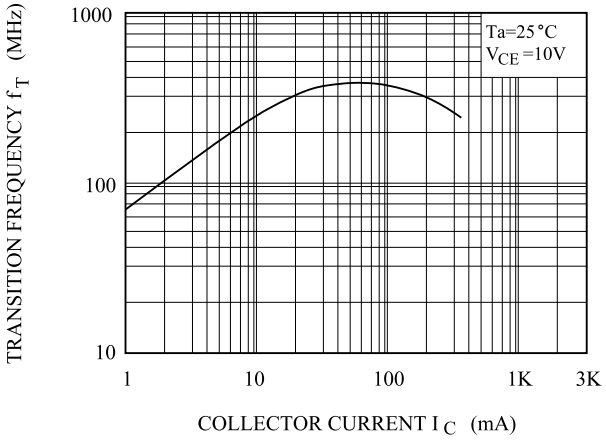
$V_{BE(sat)}$ - I_C



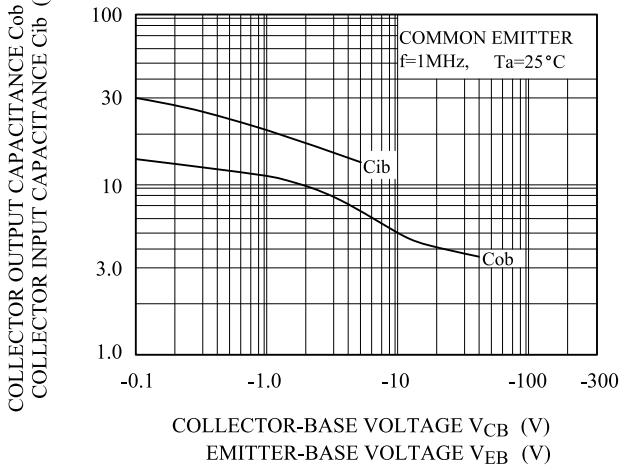
I_C - V_{BE}



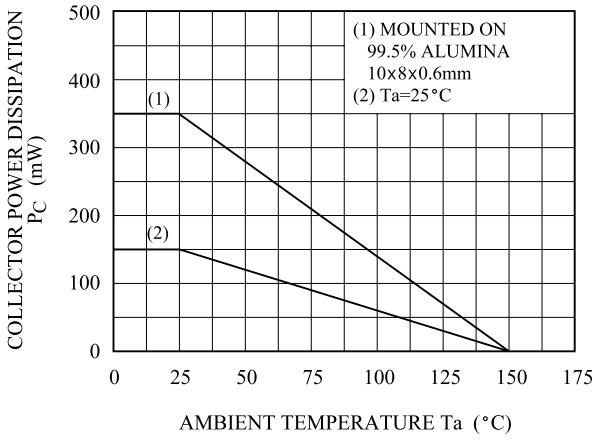
f_T - I_C



Cob - V_{CB}
Cib - V_{EB}



Pc - Ta



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